## IN THE SPECIFICATION:

Applicant notes the examiner's reference to "Page 6, line 6" but is unsure why the change is suggested. Due to the examiner's objection the Applicant has made the following change to paragraph [0028]. Please replace paragraph [0028] with the following amended paragraph:

[0028] Referring to FIG. 2, a schematic cross-sectional view of an ECP/EMP station 53a is shown in greater detail. A substrate 22 is held in place on the ECP/EMP head 64a. A partial enclosure 34 generally defines a container or electroplating cell within which a plating electrolyte may be confined.

Please replace paragraph [0048] with the following amended paragraph:

[0048] Referring to FIGS. 4a and 6, the formation of the metal layer 502 begins with step 700. The porous pad 28 contacts selective portions of the substrate 22. The porous pad 28 may contact the selective portions of the substrate with a pressure in a range of about 0.1 phi psi and about 5 psi. The porous pad 28 and the substrate 22 may rotate relative to each other. For example, the porous pad 28 and the substrate 22 may both rotate off axis to provide orbital rotation. The substrate 22 and/or the porous pad 28 may each rotate at a velocity of about 20 rpm to about 150 rpm.

Please replace paragraph [0050] with the following amended paragraph:

[0050] Concurrent with the deposition of the metal layer 502 on the substrate using ECP techniques, selected portions thereof may be polished using EMP techniques, as indicated in step 704 of FIG. 6. During the EMP process, the substrate 22 remains mounted on the ECP/EMP head 64a and immersed in the electrolyte solution used to deposit metal layer 502 thereon. The EMP process in conjunction with the ECP process functions to remove over-plated areas 502a of metal deposited on the dielectric material 602 by alternately applying a potential difference between the counter electrode  $\frac{1}{8}$   $\frac{1}{8}$  and

the working electrode w that is opposite to the polarity used to plate metal on the substrate for ECP.

Please replace paragraph [0051] with the following amended paragraph:

[0051] During EMP, the porous pad 28 may contact selective portions of the substrate 22. The porous pad 28 may contact the selective portions of the substrate with a pressure in a range of about 0.1 phi psi and about 5 phi psi. Additionally, the rotatable platen 55 with the porous pad 28 mounted thereon may be rotated at a velocity of about 20 rpm to about 150 rpm.